# Automotive HVAC

**Solution Proposal by Toshiba** 



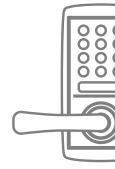






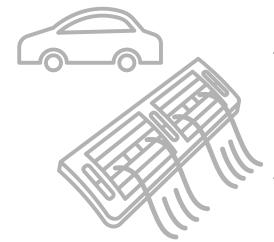




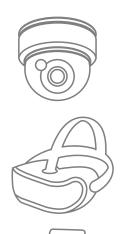






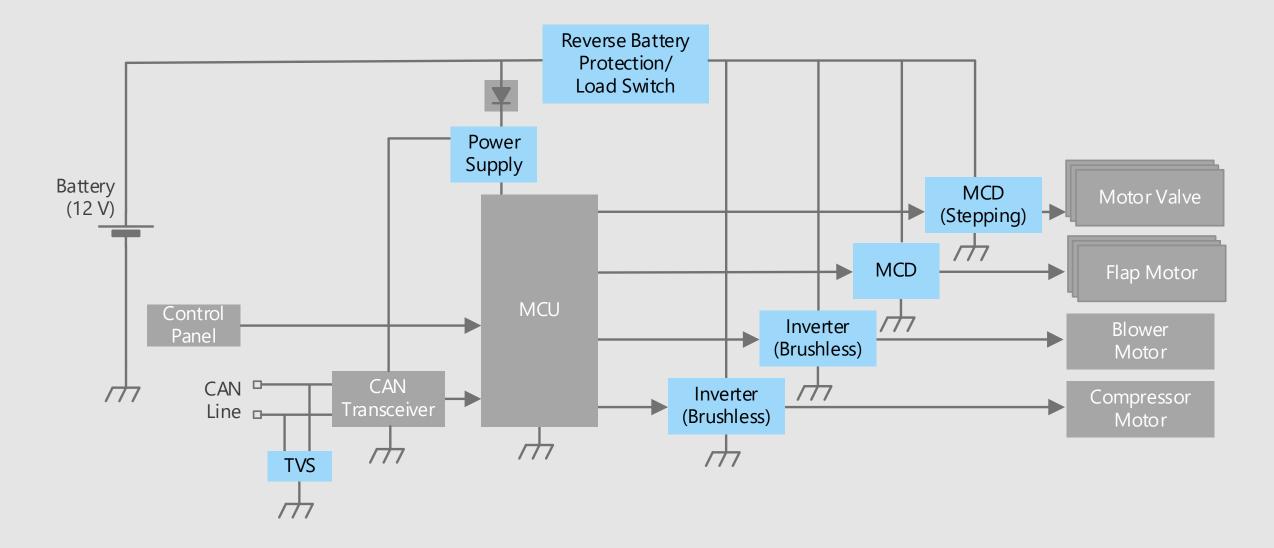


Toshiba Electronic Devices & Storage Corporation provides comprehensive device solutions to customers developing new products by applying its thorough understanding of the systems acquired through the analysis of basic product designs.



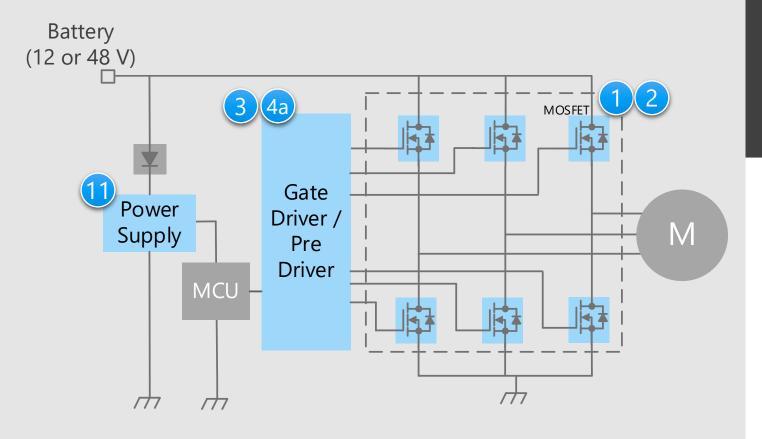
# Block Diagram

### HVAC Overall block diagram



#### Detail of brushless DC motor drive HVAC

#### **Brushless DC motor drive circuit**



\* Click on the numbers in the circuit diagram to jump to the detailed descriptions page

### Criteria for device selection

- It is necessary to select the product with the suitable voltage and current ratings for each application.
- It is necessary to select a gate driver according to the characteristics of the switching device to be driven.
- A small surface mount package is suitable for realizing miniaturization of the ECU.

### Proposals from Toshiba

-Low on-resistance contributes to low power consumption of the system

U-MOS Series 40 V N-ch MOSFET U-MOS Series 100 V N-ch MOSFET

- Gate driver with built-in protection and diagnosis functions Gate driver (for motor)

- Noise reduction by sinusoidal wave driving Brushless DC motor pre driver for blower
- Voltage regulator with low current consumption Power supply IC (for MCU)

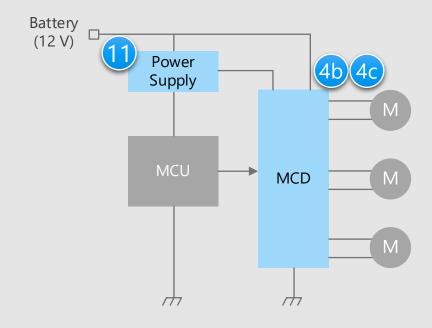






### HVAC Detail of brushed DC motor drive

#### **Brushed DC motor drive circuit**



### Criteria for device selection

- -The number of parts can be reduced by using the motor control IC with the built-in output driver.
- -A small surface mount package is suitable for realizing miniaturization of the ECU.

### Proposals from Toshiba

- -Suitable for driving a small brush DC motor
- Brushed DC motor driver for damper (4b)(4c)



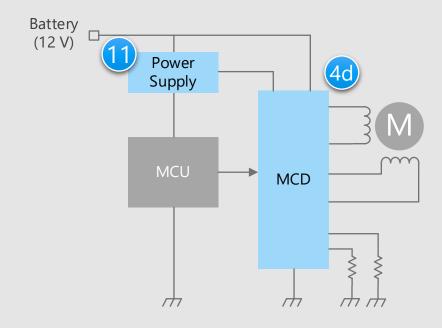
- -Voltage regulator with low current consumption
- Power supply IC (for MCU)



\* Click on the numbers in the circuit diagram to jump to the detailed descriptions page

### HVAC Detail of stepping motor drive

### **Stepping motor drive circuit**



### Criteria for device selection

- -The number of parts can be reduced by using the motor control IC with the built-in output driver.
- -A small surface mount package is suitable for realizing miniaturization of the ECU.

### Proposals from Toshiba

- -Suitable for a motor valve drive
  Stepping motor driver
- t
- -Voltage regulator with low current consumption

Power supply IC (for MCU)

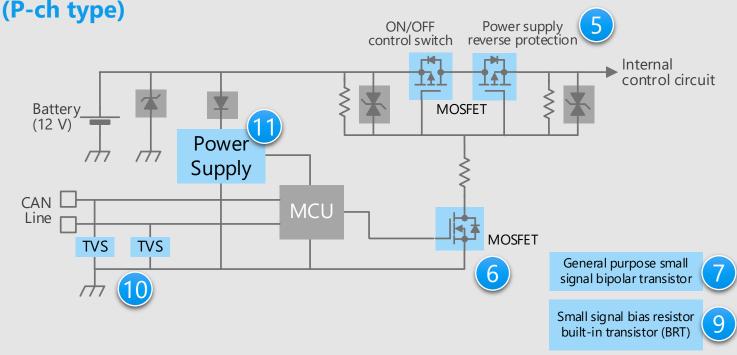
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\* Click on the numbers in the circuit diagram to jump to the detailed descriptions page

### HVAC

### Detail of switch for power supply ON/OFF control and reverse connection protection (1)

### **Power supply ON/OFF control and** reverse connection protecting circuit



\* Click on the numbers in the circuit diagram to jump to the detailed descriptions page

### Criteria for device selection

- It is necessary to select the product with the suitable voltage and current ratings for each application.
- It is necessary to select a gate driver according to the characteristics of the switching device to be driven.
- A small surface mount package is suitable for realizing miniaturization of the ECU.

### Proposals from Toshiba

-Low on-resistance contributes to low power consumption of the system

U-MOS Series -40 V / -60 V P-ch MOSFET

- Extensive product lineup General purpose small signal MOSFET General purpose small signal bipolar transistor

Small signal bias resistor built-in transistor (BRT)

-Suitable for ESD protection TVS diode (for CAN communication)

- Voltage regulator with low current consumption Power supply IC (for MCU)









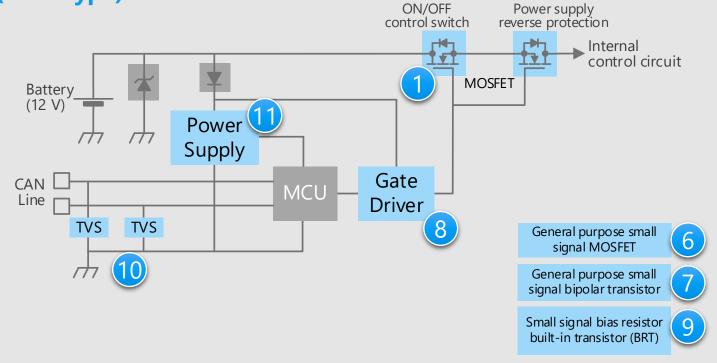




### HVAC

### Detail of switch for power supply ON/OFF control and reverse connection protection (2)

## Power supply ON/OFF control and reverse connection protecting circuit (N-ch type)



\* Click on the numbers in the circuit diagram to jump to the detailed descriptions page

### Criteria for device selection

- -It is necessary to select the product with the suitable voltage and current ratings for each application.
- It is necessary to select a gate driver according to the characteristics of the switching device to be driven.
- A small surface mount package is suitable for realizing miniaturization of the ECU.

### Proposals from Toshiba

- Low on-resistance contributes to low power consumption of the system
   U-MOS Series 40 V N-ch MOSFET
- Gate driver with built-in protection and diagnosis functions
   Gate driver (for switch)
- -Extensive product lineup
  General purpose small signal MOSFET
  General purpose small signal bipolar transistor
  Small signal bias resistor built-in transistor (BRT)
- Suitable for ESD protection
   TVS diode (for CAN communication)
- -Voltage regulator with low current consumption Power supply IC (for MCU)















### Device solutions to address customer needs

As described above, in the design of HVAC, "Ensuring tolerance to motor lock current. Capable with functional safety", "Reduction of power consumption" and "Miniaturization" are important factors. Toshiba's proposals are based on these three solution perspectives.

Ensuring tolerance to motor lock current.

Capable with functional safety



Reduction of power consumption



Miniaturization



### Device solutions to address customer needs

	Robustness	High efficiency - Low loss	Small size package
U-MOS Series 40 V N-ch MOSFET			
U-MOS Series 100 V N-ch MOSFET			
Gate driver (for motor)			
Motor driver *			
U-MOS Series -40 V / -60 V P-ch MOSFET			
General purpose small signal MOSFET			
General purpose small signal bipolar transistor			
Gate driver (for switch)			
Small signal bias resistor built-in transistor (BRT)			
TVS diode (for CAN communication)			
Power supply IC (for MCU)			
	U-MOS Series 100 V N-ch MOSFET  Gate driver (for motor)  Motor driver *  U-MOS Series -40 V / -60 V P-ch MOSFET  General purpose small signal MOSFET  General purpose small signal bipolar transistor  Gate driver (for switch)  Small signal bias resistor built-in transistor (BRT)  TVS diode (for CAN communication)	U-MOS Series 40 V N-ch MOSFET U-MOS Series 100 V N-ch MOSFET Gate driver (for motor)  Motor driver *  U-MOS Series -40 V / -60 V P-ch MOSFET General purpose small signal MOSFET General purpose small signal bipolar transistor Gate driver (for switch)  Small signal bias resistor built-in transistor (BRT)  TVS diode (for CAN communication)	U-MOS Series 40 V N-ch MOSFET U-MOS Series 100 V N-ch MOSFET Gate driver (for motor)  Motor driver *  U-MOS Series -40 V / -60 V P-ch MOSFET  General purpose small signal MOSFET  General purpose small signal bipolar transistor  Gate driver (for switch)  Small signal bias resistor built-in transistor (BRT)  TVS diode (for CAN communication)

<sup>\*</sup> Damper (LIN communication): TB9056FNG / TB9058FNG, (Direct control type): TB9101FNG / TB9102FNG

<sup>\*</sup> Blower: TB9080FG

<sup>\*</sup> Expansion valves in refrigerant cooling system: TB9120AFTG

### **U-MOS Series 40 V N-ch MOSFET**

XPN3R804NC / TK1R4S04PB / XPHR7904PS / TPWR7904PB / XPJ6604PB\* / XPQR3004PB







Value provided

### The latest processes enables low on-resistance and low noise, thereby reducing power consumption.

### **Low loss** (reduced on-resistance)

Using low on-resistance technology to contribute to reduced power consumption systems.

On-resistance of 44 % reduction per unit area. (compared to Toshiba's U-MOSWI-H products)

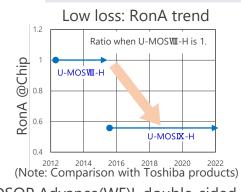
### **Small and low loss package**

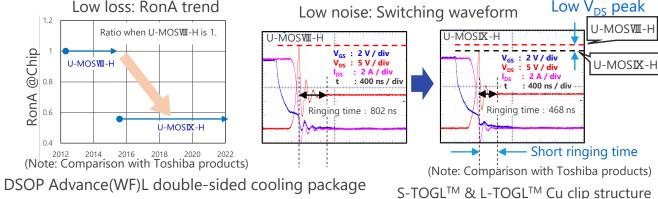
By adopting a Cu clip structure and a doublesided heat dissipation structure, low loss and high heat dissipation are realized. Wettable Flank (WF) package contributes to good mountability.

**Postless** 

### Low noise (low EMI)

Improved chip process reduces surge voltage and ringing time.





Post (solder connection)

Cu connector

**High Current & Low resistance** 

1	Lineup			
_ -	Part number	Rated drain current [A]	On-resistance (Max) [m $\Omega$ ] @V <sub>GS</sub> = 10 V	Package
_	XPN3R804NC	40	3.8	TSON Advance(WF)
	TK1R4S04PB	120	1.35	DPAK+
	XPHR7904PS	150	0.79	SOP Advance(WF)
	TPWR7904PB	150	0.79	DSOP Advance(WF)L
	XPJR6604PB*	(200)	(0.66)	S-TOGL™
	XPQR3004PB	400	0.30	L-TOGL™ ♠

\*: Under development (Values enclosed in parentheses are tentative specifications. Specifications are subject to change without notice.)

◆Return to Block Diagram TOP



Thermal resistance is reduced 76% @t = 3 s, mounted on board Compared to Toshiba's SOP Advance(WF)

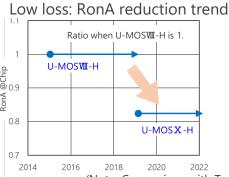


### Low on-resistance contributes to reduced system power consumption.

### Low loss (reduced on-resistance)

Using low on-resistance technology to contribute to reduced power consumption systems.

On-resistance per unit area has been reduced by 18 %. (compared to Toshiba's U-MOSVIII-H products)



Small and high power dissipation package

SOP L-TOGL<sup>TM</sup> DPAK+ Advance(WF) (9.9 x 11.8 mm)  $(6.5 \times 10 \text{ mm})$  $(5 \times 6 \text{ mm})$ Up to 300 A Up to 60 A Up to 70 A

Wettable

(Note: Comparison with Toshiba products)

DSOP Advance(WF)L double-sided cooling packages

Thermal resistance is reduced 76 % @t = 3 s, mounted on board Cu connector (Compared to Toshiba's SOP Advance(WF)

L-TOGL<sup>™</sup> Cu clip structure **High current & Low resistance** 



Post (solder connection)

### **Post less**

### Small and high power dissipation package

The small and high power dissipation packages are developed by adopting Cu clip or Cu connector structure.

Wettable Flank (WF) package contributes to good mountability.

Lineup			
Part number	Rated drain current [A]	On-resistance (Max) $[m\Omega] @V_{GS} = 10 \text{ V}$	Package
XPN1300ANC	30	13.3	TCONI A di ser es (IAIT)
XPN2400ANC *	(20)	(23.5)	TSON Advance(WF)
TK60S10N1L	60	6.11	DPAK+
XPH4R10ANB	70	4.1	COD Advisor on (ME)
XPH6R30ANB	45	6.3	SOP Advance(WF)
XPW4R10ANB	70	4.1	DSOP Advance(WF)L
XPW6R30ANB	45	6.3	DSOP Advance(WF)M
XPQ1R00AQB *	(300)	(1.03)	L-TOGL™

<sup>\*:</sup> Under development (Values enclosed in parentheses are tentative specifications. Specifications are subject to change without notice.)







### The high gate drive current capability reduces MOSFET losses and improves the efficiency of system.

### High gate drive current

High drive current capability and high speed switching contribute to reduce the loss.

TPD7211F: ±0.5 A

TPD7212F, TPD7212FN: -1 / +1.5 A

### Built-in protection /diagnostic output function

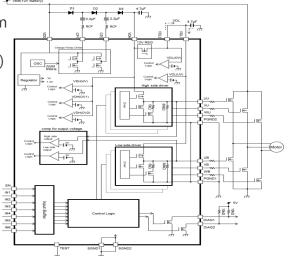
MOSFET is turn off when a signal is input that causes arm short circuit.

Functions to monitor abnormalities of the power supply voltage and output voltage are built-in.

### Small surface mount package

PS-8, WQFN32 and SSOP30 are small surface mount packages. They contribute to the miniaturization of system.

Example of application and block diagram of TPD7212F, TPD7212FN (Three phase brushless DC motor control)



Lineup		
Part number	TPD7211F	TPD7212F / TPD7212FN
Function	Half bridge output gate driver	Gate driver for three-phase brushless motor
Number of output	2 outputs	6 outputs
Package	PS-8 (2.8 x 2.9 mm)	TPD7212F TPD7212FN Back surface P-WQFN32-0505-0.50-002 SSOP30-P-300-0.65
Features	·For high side P-ch MOSFET drive	<ul> <li>For driving high side N-ch MOSFET         (with built-in charge pumps)</li> <li>Built-in voltage monitoring function         (power supply, output)</li> </ul>







This is suitable for applications as air conditioner blower motors or battery cooling fans, that required quietness and high efficiency.

Support two types of rotation control input

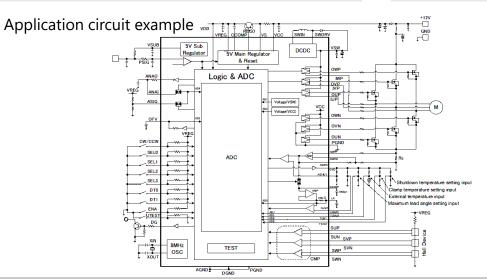
The motor speed control is compatible with both PWM [Note] signal input and DC voltage input.

[Note] Pulse Width Modulation

No microcontroller required

Since a microcontroller is not required, the area of control board can be reduced and the program development period can be shortened. **Various built-in detection functions** 

Built-in various detection functions such as overcurrent, overtemperature, over voltage, and under voltage.



Lineup	
Part number	TB9080FG
Package	LQFP64-P-1010-0.50E (12 x 12 mm)
Operating voltage range [V]	7 to 18
Sleep consumption current (Typ.) [μΑ]	50
Number of external MOSFETs	N-ch x 6
Drive control	Sine wave control





### It has built-in output MOSFETs and can drive brushed DC motor directly.

### Built-in output MOSFETs

It has built-in output MOSFETs and can drive brushed DC motor directly.

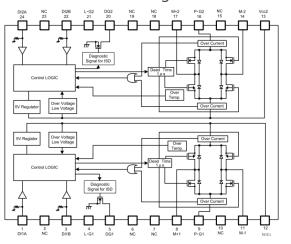
### **Description** Low on-resistance

Low on-resistance contributes to reduce heat generation and power consumption.

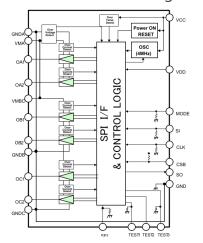
### **Yarious built-in detection** functions

Built-in various detection functions such as overcurrent, overtemperature, over voltage and under voltage.

#### TB9101FNG block diagram



#### TB9102FNG block diagram



Lineup		
Part number	TB9101FNG	TB9102FNG
Package	SSOP24-P-300-0.65A (7.6 x 8.3 mm)	September 1
Power supply voltage [V]	7 to 18	7 to 18
Output current [A]	±1.0	±1.0
Allowable power dissipation [W]	1.32	1.32
On-resistance (High side / Low side) (Typ.) $[\Omega]$	0.6 / 0.6	0.5 / 0.5
External interface	Direct input	SPI interface







#### This is full hardware brushed DC motor driver with LIN communication function.

### Simple control by full hardware

No need to develop software. Motor control by LIN communication (slave).

### **2** Low on-resistance and low standby current

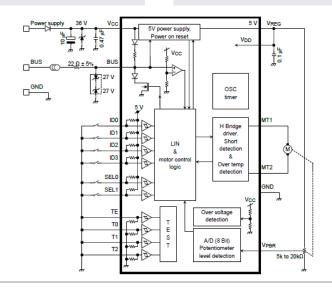
On-resistance: 2.2  $\Omega$  (Typ.) (High side + Low side)

Standby current: 10 µA (Max)

### **3** Various built-in detection functions

Built-in various detection functions such as over current, over temperature, over voltage and under voltage.

TB9056FNG / TB9058FNG block diagram



Lineup					
Part number	TB9056FNG	TB9058FNG			
Package	SSOP24-P-300-0.65A				
Power supply voltage [V]	7 to 18	7 to 18			
Output current [A]	0.3	0.3			
Motor drive circuit type	H-bridge (1ch)	H-bridge (1ch)			
On-resistance (High side / Low side) (Typ.) $[\Omega]$	1.0 / 1.2	1.0 / 1.2			
Communication method	LIN rev. 1.3	LIN rev. 1.3 (Enhanced checksum)			







### Micro stepping drive controlled by single clock input signal only.

### Micro stepping drive

Full step to 1/32 step which contributes to reducing noise and vibration is supported.

Neither high performance MCUs nor software are required. It can be controlled by clock signal.

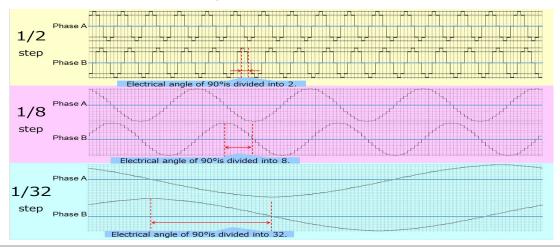
### **Stall detection**

A detection signal is output, if the IC judges a malrotation.

### **3** Broad utility

It can be used for various applications.
Application example
Dampers
Expansion valves
Head-up Display (HUD)

#### Current waveform in micro step



Lineup						
Part number	TB9120AFTG					
Package	P-VQFN28-0606-0.65-002 6 x 6 mm Wettable flank package contributes to good solderability.					
Output device	Built-in MOSFETs for 1 A class					
Output MOSFET on-resistance	0.8 $\Omega$ (Typ.) (High side + Low side, Ta = 25 °C)					
Detection circuit	Over current, over temp., stall detection and load open					
Standby function	Current consumption less than 10 µA in standby mode Built-in a standby pin					

### U-MOS Series -40 V / -60 V P-ch MOSFET XPN9R614MC / XPH3R114MC / XPH8R316MC\* / TJ90S04M3L



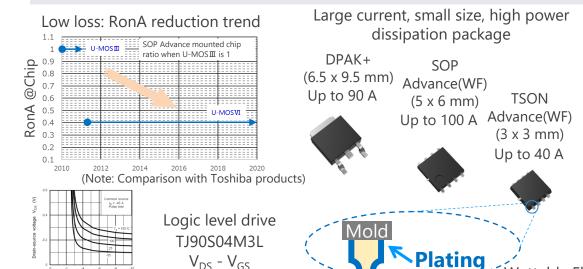
Value provided

### Low on-resistance contributes to reduce system power consumption.

### Low loss (reduced on-resistance) and logic level drive

Using a low on-resistance technology contributes to reduce system power consumption.

A lineup of logic level drive type is supported. The on-resistance per area is reduced by 60 %. (compared to Toshiba's U-MOSIII products)



### **Small and low loss packages**

By adopting a Cu connector structure, a low loss and high power dissipation package is realized.

Wettable Flank (WF) package contributes to good mountability.

Lineup								
Part number	Rated drain-source voltage [V]	Rated drain current [A]	On-resistance (Max) $[m\Omega]$ @V <sub>GS</sub> = -10 V	Package				
XPN9R614MC	-40	-40	9.6	TSON Advance(WF)				
XPH3R114MC	-40	-100	3.1	COD Advance(IMF)				
XPH8R316MC*	-60	(-90)	(8.3)	SOP Advance(WF)				
TJ90S04M3L	-40	-90	4.3	DPAK+				

<sup>\*:</sup> Under development (Values enclosed in parentheses are tentative specifications. Specifications are subject to change without notice.)



### General purpose small signal MOSFET SSM3K7002KF / SSM3J168F / SSM3J66MFV







Value provided

### Wide lineup of small packages contribute to reduce the size and power consumption of system.

### Small package

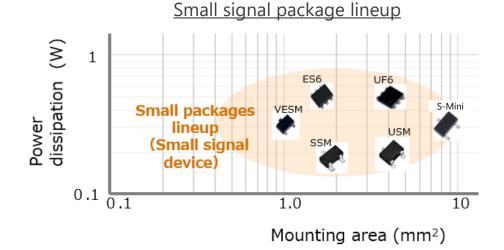
A lineup of various small packages such as SOT-723 (VESM 1.2 x 1.2 mm package) is available, contributing to reduce mounting area.

### **Description**Low voltage drive

SSM3J66MFV can be driven at low gatesource voltage of 1.2 V.

### **3** AEC-Q101 qualified

AEC-Q101 qualified and can be used for various automotive applications.



Lineup							
Part number	Part number		SSM3J168F	SSM3J66MFV			
Package		S-Mini (SOT-346)	S-Mini (SOT-346)	VESM (SOT-723)			
V <sub>DSS</sub> [V]		60	-60	-20			
I <sub>D</sub> [A]		0.4	-0.4	-0.8			
R <sub>DS(ON)</sub>	Тур.	1.2	1.4	0.31			
$@ V_{GS}  = 4.5 V [Ω]$ Max		1.75	1.9	0.39			
Drive voltage [V]		4.5	-4.0	-1.2			
Polarity		N-ch	P-ch	P-ch			



### General purpose small signal bipolar transistor 25C2712 / 25A1162 / 25C4116 / 25A1586 / TTA501 / TTC501 and others







Value provided

### Extensive product lineup to meet customers' needs.

### **Extensive lineup of packages**

Various packages such as 1-in-1, 2-in-1 are provided and suitable products for circuit board design are selectable.

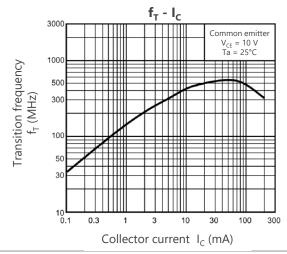
### **Extensive product lineup**

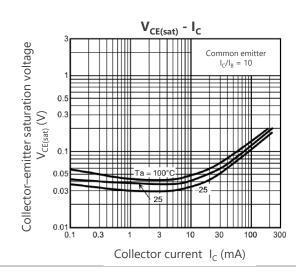
Various product lineups, such as general purpose, low noise, low  $V_{\text{CE(sat)}}$  and high current types are provided. Products can be selected in accordance with the application.

### AEC-Q101 qualified

AEC-Q101 qualified and can be used for various automotive applications.

#### **Characteristic examples of 2SC2712**





Lineup								
Package		SOT	-23F		OT-323) OT-323F)*	S-Mini (S	SOT-346)	
Classification	V <sub>CEO</sub>   [V]	I <sub>C</sub>   [mA]	NPN	PNP	NPN	PNP	NPN	PNP
Conoral nurnoso	50	150			2SC4116	2SA1586	2SC2712	2SA1162
General purpose	50	500					2SC3325	2SA1313
Low noise	120	100			2SC4117	2SA1587	2SC2713	2SA1163
	50	1700				2SA2195*		
High current	50	2000		TTA501				
	50	2500	TTC501					

<sup>\*</sup> indicates UFM package







A charge pump circuit for the N-ch MOSFET gate drive is built in, allowing for easy semiconductor relay configuration.

Built-in charge pump circuit

Built-in charge pump circuit enables N-ch MOSFET as high side switch.

Easy to configure a semiconductor relay.

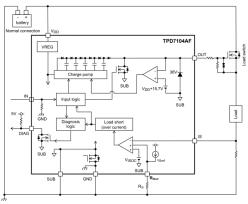
2 Can be controlled by logic level voltage

It is possible to be controlled directly by output signal of MCUs or CMOS logic ICs.

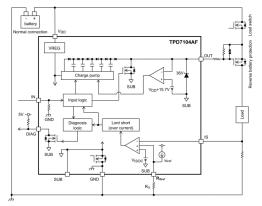
**3** Small package

The small surface mount packages such as PS-8, SSOP16 and WSON10A contribute to the miniaturization of equipment.

Semiconductor relay (switch) application (TPD7104AF)



Power supply reverse connection protection MOSFET control (TPD7104AF)



Back to back configuration

Lineup								
Part number	TPD7104AF	TPD7106F	TPD7107F					
Package	PS-8 (2.8 x 2.9 mm)	SSOP16 (5.5 x 6.4 mm)	WSON10A (3 x 3 mm)					
Function	High side gate driver	High side gate driver	High side gate driver					
Output	ıt 1 1		1					
Features	Operating power supply voltage range: 5 to 18 V     Built-in power supply reverse connection protection function (Protective MOSFET control with back-to-back circuitry)	Operating power supply voltage range: 4.5 to 27 V     Built-in power supply reverse connection protection function (Protective MOSFET control with back-to-back circuitry)	Operating power supply voltage range: 5.75 to 26 V     Current sense output     Protective functions; overcurrent, overtemperature, GND disconnect, etc. reverse battery connection     Diagnosis output; overcurrent, load open, overtemperature, etc.					

### Small signal bias resistor built-in transistor (BRT) RN1907FE / RN2907FE / RN1901 / RN2901 Series







Value provided

#### **Extensive product lineup to meet customers' needs.**

Built-in bias resistor type
(BRT: Bias Resistor built-in Transistor)

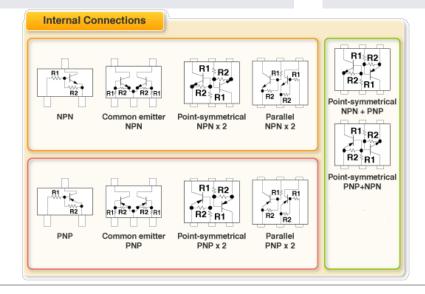
The BRTs contribute to reduction of the number of components, assembly workload and mounting area of circuit boards.

**2** Extensive lineup of package and pin assignment

Various package lineups, such as 1-in-1, 2-in-1 and various pin assignment type are provided and suitable products for circuit board design are selectable.

**3** AEC-Q101 qualified

AEC-Q101 qualified and can be used for various automotive applications.



Lineup				
Part number		NPN (BRT)	PNP (BRT)	
Package	ES6 (SOT-563)	RN1907FE	RN2907FE	
	US6 (SOT-363)	RN1901	RN2901	
V <sub>CEO</sub> [V]		50	-50	
I <sub>C</sub> [mA]		100	-100	







### TVS diodes prevent system damage and malfunction caused by electrostatic discharge (ESD).

### Improve ESD pulse absorbability

Toshiba proprietary Zener process improves the ESD pulse absorption of TVS diodes. (Achieving both low dynamic resistance  $R_{\text{DYN}}$  and low capacitance between terminals  $C_{t}$ )

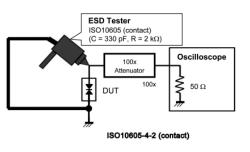
### Supports CAN, CAN FD and FlexRay

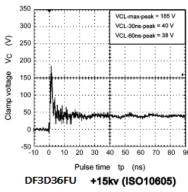
These are products applicable to invehicle LAN communication such as CAN, CAN FD and FlexRay.

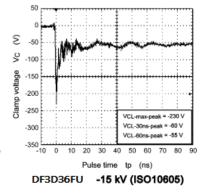
### **3** High ESD immunity

 $V_{ESD} > \pm 30 \text{ kV @ISO } 10605$ 

 $V_{ESD} > \pm 20 \text{ kV @IEC } 61000-4-2 \text{ (Level 4)}$ 







Lineup					
Part number	DF3D18FU	DF3D29FU	DF3D36FU		
Package	USM (SOT-323)				
V <sub>ESD</sub> [kV] @ISO 10605	±30	±30	±20		
V <sub>RWM</sub> (Max) [V]	12	24	28		
C <sub>t</sub> (Typ. / Max) [pF]	9 / 10		6.5 / 8		
R <sub>DYN</sub> (Typ.) [Ω]	0.8	1.1	1.5		

(Note) The above characteristics curves are presented for reference only and not guaranteed by production test, unless otherwise noted. This product is an ESD protection diode and cannot be used for purposes other than ESD protection.



This is voltage regulator with low current consumption, and various monitoring functions such as WDT [Note] contribute to improving system stability.

### Low current consumption

External transistor type voltage regulator with low current consumption.

Load stability is 1 % (Max) (@ILOAD = 1 to 300 mA).

### **2** Built-in WDT and various monitoring functions

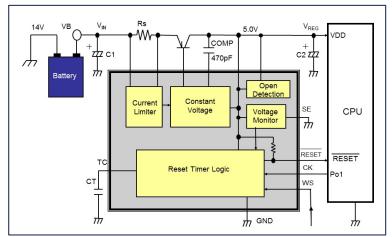
The WDT monitors the operation of the MCU.

In addition, current detection functions contribute to improving system stability.

### **3** AEC-Q100 qualified

It is AEC-Q100 qualified and can be used for various automotive applications.

Application circuit example (The current limiter can be adjusted by an external resistor.)



Lineup				
	Part number	TB9005FNG		
	Package	SSOP20-P-225-0.65A (6.4 x 7.0 mm)		
Curren	t consumption I <sub>CC</sub> (Typ.) [μΑ]	90 (@V <sub>IN</sub> = 12 V, Ta = 25 °C)		
Load	stability VLOAD (Max) [%]	1 (@ILOAD = 1 to 300 mA)		
u C	Number of outputs	1ch (5 V)		
Function	Circuit type	External transistor type		
	WDT, Overcurrent limitation	✓		

If you are interested in these products and have questions or comments about any of them, please do not hesitate to contact us below:

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